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	ute for form 1449B			Complete if Known				
				Application Number	10/809,650			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	25 March 2004			
				First Named Inventor	Michel Cote et al.			
0.,				Group Art Unit	unknown	<u> </u>		
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Sheet	t	of	3	Attorney Docket Number	NMTI 1002-27			

		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS	
Examiner Initiats*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Τ7
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Signature	Considered	<u> </u>

[‡] Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.



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Examiner Initials*	Cite No.1	item (book, magazine, journal, serial, symposium, catalog, atc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T2					
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